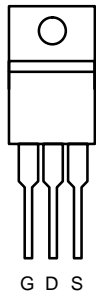




N-Channel 60-V (D-S), 175 °C MOSFET

PRODUCT SUMMARY		
$V_{(BR)DSS}$ (V)	$r_{DS(on)}$ (Ω)	I_D (A)
60	0.014	70 ^a

TO-220AB

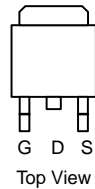


Top View

SUP70N06-14

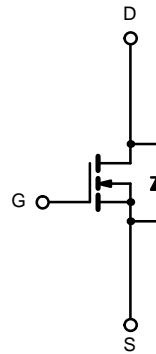
DRAIN connected to TAB

TO-263



Top View

SUB70N06-14



N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS ($T_C = 25^\circ\text{C}$ UNLESS OTHERWISE NOTED)			
Parameter	Symbol	Limit	Unit
Gate-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current ($T_J = 175^\circ\text{C}$)	I_D	$T_C = 25^\circ\text{C}$	70 ^a
		$T_C = 100^\circ\text{C}$	49
Pulsed Drain Current	I_{DM}	160	A
Avalanche Current	I_{AR}	70	
Repetitive Avalanche Energy ^b	E_{AR}	L = 0.1 mH	180
Power Dissipation		$T_C = 25^\circ\text{C}$ (TO-220AB and TO-263)	142 ^c
	$T_A = 25^\circ\text{C}$ (TO-263) ^d	3.7	
Operating Junction and Storage Temperature Range	T_J, T_{stg}	-55 to 175	$^\circ\text{C}$

THERMAL RESISTANCE RATINGS			
Parameter	Symbol	Limit	Unit
Junction-to-Ambient	R_{thJA}	PCB Mount (TO-263) ^d	40
		Free Air (TO-220AB)	62.5
Junction-to-Case	R_{thJC}	1.05	$^\circ\text{C/W}$

Notes:

- a. Package limited.
- b. Duty cycle $\leq 1\%$.
- c. See SOA curve for voltage derating.
- d. When mounted on 1" square PCB (FR-4 material).

For SPICE model information via the Worldwide Web: <http://www.vishay.com/www/product/spice.htm>



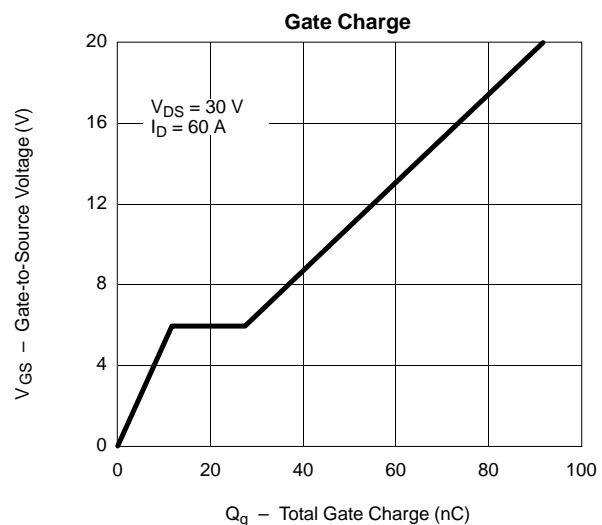
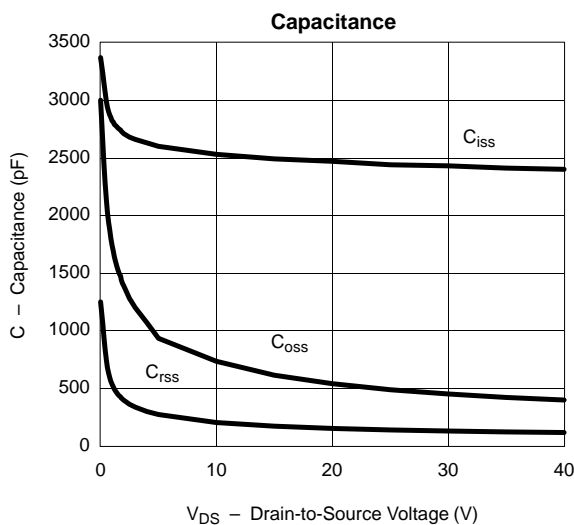
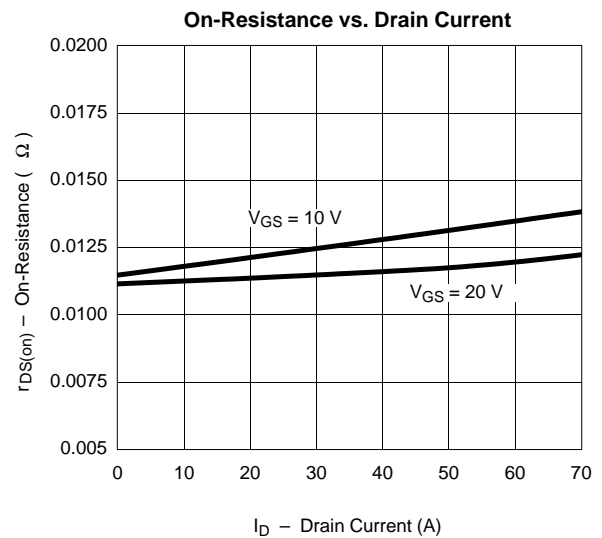
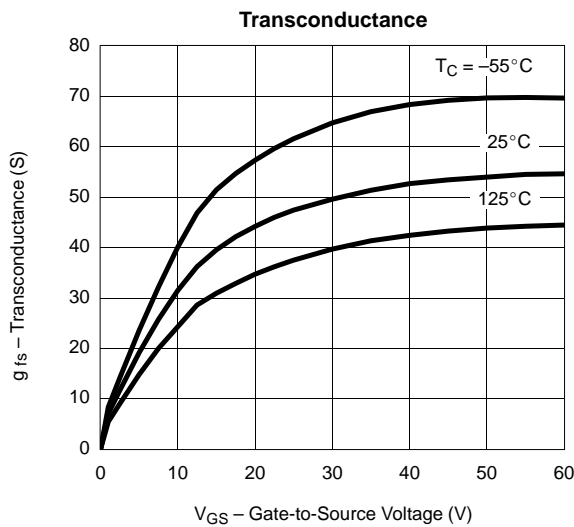
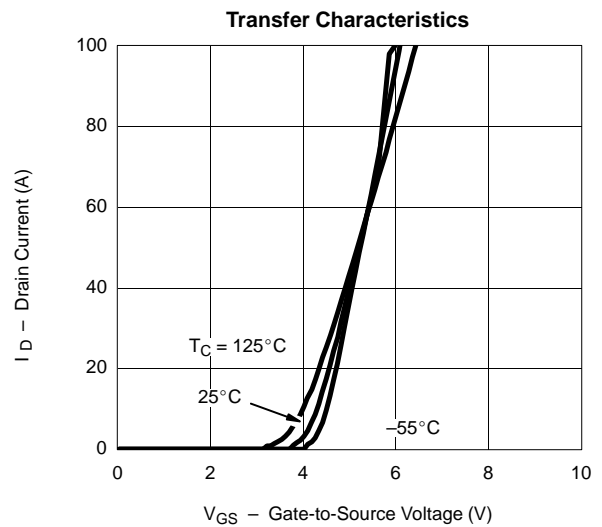
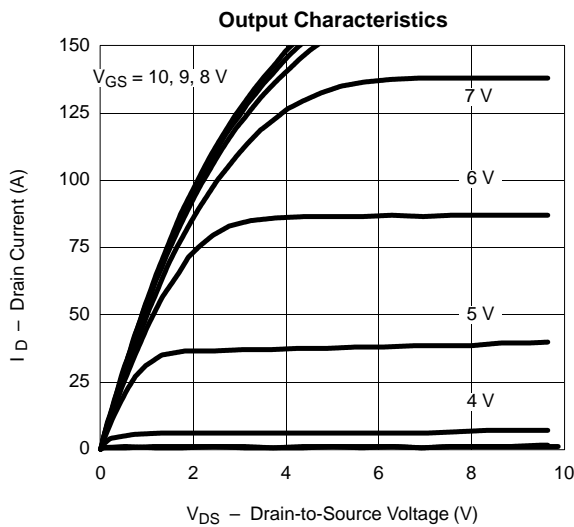
SPECIFICATIONS (T _J = 25 °C UNLESS OTHERWISE NOTED)							
Parameter	Symbol	Test Condition	Min	Typ	Max	Unit	
Static							
Drain-Source Breakdown Voltage	V _{(BR)DSS}	V _{GS} = 0 V, I _D = 250 μA	60			V	
Gate Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _{DS} = 1 mA	2.0	3.0	4.0		
Gate-Body Leakage	I _{GSS}	V _{DS} = 0 V, V _{GS} = ±20 V			±100	nA	
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 60 V, V _{GS} = 0 V			1	μA	
		V _{DS} = 60 V, V _{GS} = 0 V, T _J = 125 °C			50		
		V _{DS} = 60 V, V _{GS} = 0 V, T _J = 175 °C			150		
On-State Drain Current ^a	I _{D(on)}	V _{DS} = 5 V, V _{GS} = 10 V	70			A	
Drain-Source On-State Resistance ^a	r _{DS(on)}	V _{GS} = 10 V, I _D = 30 A			0.014	Ω	
		V _{GS} = 10 V, I _D = 30 A, T _J = 125 °C			0.023		
		V _{GS} = 10 V, I _D = 30 A, T _J = 175 °C			0.028		
Forward Transconductance ^a	g _{fs}	V _{DS} = 15 V, I _D = 30 A	25	50		S	
Dynamic^b							
Input Capacitance	C _{iss}	V _{GS} = 0 V, V _{DS} = 25 V, f = 1 MHz		2400		pF	
Output Capacitance	C _{oss}			490			
Reverse Transfer Capacitance	C _{rss}			130			
Total Gate Charge ^c	Q _g	V _{DS} = 30 V, V _{GS} = 10 V, I _D = 60 A		45	70	nC	
Gate-Source Charge ^c	Q _{gs}			12			
Gate-Drain Charge ^c	Q _{gd}			16			
Turn-On Delay Time ^c	t _{d(on)}	V _{DD} = 30 V, R _L = 0.47 Ω I _D = 60 A, V _{GEN} = 10 V, R _G = 2.5 Ω		13	30	ns	
Rise Time ^c	t _r			11	30		
Turn-Off Delay Time ^c	t _{d(off)}			30	60		
Fall Time ^c	t _f			11	25		
Source-Drain Diode Ratings and Characteristics (T_C = 25 °C)^b							
Continuous Current	I _s				70	A	
Pulsed Current	I _{SM}				160		
Forward Voltage ^a	V _{SD}	I _F = 70 A, V _{GS} = 0 V			1.4	V	
Reverse Recovery Time	t _{rr}	I _F = 60 A, di/dt = 100 A/μs		47		ns	
Peak Reverse Recovery Current	I _{RM(REC)}				3.5		A
Reverse Recovery Charge	Q _{rr}				0.08		μC

Notes:

- a. Pulse test; pulse width ≤ 300 μs, duty cycle ≤ 2%.
- b. Guaranteed by design, not subject to production testing.
- c. Independent of operating temperature.

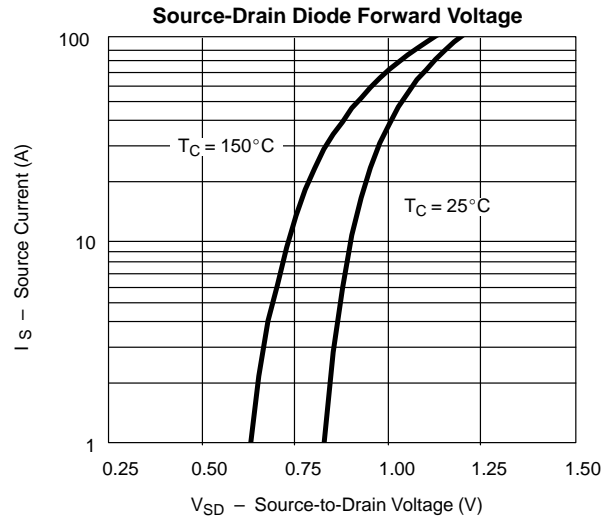
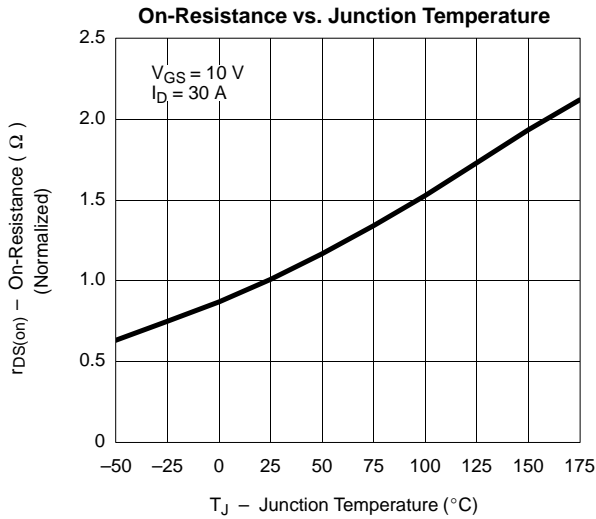


TYPICAL CHARACTERISTICS (25°C UNLESS NOTED)





TYPICAL CHARACTERISTICS (25°C UNLESS NOTED)



THERMAL RATINGS

